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Quantum Conductance of the Single Electron Transistor

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The quantum conductance of the single-electron tunneling (SET) transistor is investigated in this paper by the functional integral approach. The formalism is valid for arbitrary tunnel resistance of the junctions forming the SET transistor at any temperature. The path integrals are evaluated by the semiclassical method to yield an explicit non-perturbation form of the quantum conductance of the SET transistor. An anomaly of the quantum conductance is found if the tunnel resistances are much smaller than the quantum resistance. The dependence of the conductance on the gate voltage is also discussed.

Coulomb blockade effects in systems containing ultrasmall tunnel junctions have attracted great interest in recent years[1–3]. The basic device to show the transport properties of such structures is the single electron tunneling transistor (SET-transistor), where an ultrasmall metallic island is formed by two in-series connected tunnel junctions. The island is coupled to a gate voltage V_G via a capacitance C_G. A transport voltage V is attached, say, to the left lead electrode. The behavior of the SET-transistor has been investigated extensively both theoretically and experimentally[4–7]. Most of the works have concentrated on the case of high tunnel resistances and low temperatures in order to satisfy the conditions $R_T \gg R_K = h/e^2$ and $k_B T \ll e^2/2C$ with C of the same order of C_G or capacitances of the tunnel junctions so that Coulomb blockade effects are obviously not washed out[3]. Under these conditions, however, the speed of controlable tunneling processes is strongly limited and present devices must work at very low temperatures. On the other hand, the latest experiments show that the manifestation of Coulomb blockade at high temperatures is clearly observable, even for strong tunneling, and such effects are of significant applications[8,9]. Therefore it is meaningful to investigate such systems with various tunneling strengths and temperatures.

The SET-transistor in the presence of an infinitesimal transport voltage may be described by the Hamiltonian $H = H_0 + H_T$[2,10] , where $H_0 = H_L + H_R + H_I + H_Q$ represents systems in the absence of tunneling. Here H_L, H_R and H_I describe the free quasi-particles on the left lead electrode, right lead electrode and on the island formed by the tunnel junctions, respectively. H_Q is the Coulomb energy of the SET-transistor with the form $H_Q = E_c(q/e - n_{\rm ex})^2$, where $E_c = e^2/2C_\Sigma$ with the total capacitance $C_\Sigma = C_L + C_R + C_G$. The influence of the continuous change of the gate voltage is described by $n_{\rm ex} = C_G V_G/e$ and q is the charge operator on the island.

The tunneling Hamiltonian contains two parts describing tunneling processes between the left lead electrode and the island

$$\begin{aligned} H_{T1}(\varphi_1) &= H^+_{T1}(\varphi_1) + H^-_{T1}(\varphi_1) \\ &= \sum_{kq\sigma} (t_{kq\sigma} c^+_{k\sigma} c_{q\sigma} e^{-i\varphi_1} + h.c.) \end{aligned} \tag{1}$$

and tunneling processes between the island and the right lead electrode

$$\begin{aligned} H_{T2}(\varphi_2) &= H^+_{T2}(\varphi_2) + H^-_{T2}(\varphi_2) \\ &= \sum_{k'q\sigma} (t_{k'q\sigma} c^+_{k'\sigma} c_{q\sigma} e^{-i\varphi_2} + h.c.). \end{aligned} \tag{2}$$

Here k, k' and q are the longitudinal wave numbers, σ denotes the transversal and spin numbers, φ_i is the phase of the i-th tunnel junction conjugate to the charge of it Q_i. The conservation of σ during tunneling processes is included in the above equations. Since the typical impedance of the external electromagnetic environment is much smaller than R_K, its influence on the quantum conductance of the SET-transistor may normally be neglected[11,12].

Let us now introduce the total phase $\Psi = \varphi_1 + \varphi_2 = e\int_{-\infty}^{t} dt' V(t')$ conjugate to the total charge $Q = \kappa_1 Q_1 + \kappa_2 Q_2$, and the phase $\varphi = \kappa_2\varphi_1 - \kappa_1\varphi_2$ as a conjugate variable to the island charge q. Here $\kappa_1 = (C_R + C_G/2)/C_\Sigma$, and $\kappa_2 = (C_L + C_G/2)/C_\Sigma$. Then the perturbation Hamiltonian as a linear function of the transport voltage reads

$$\delta H_T = \Psi F(\varphi) + \mathcal{O}(\Psi^2), \tag{3}$$

with the generalized force

$$F(\varphi) = [\kappa_1 I_1(\varphi) - \kappa_2 I_2(\varphi)]/e, \tag{4}$$

where the tunnel current from the left lead electrode to the island is

$$I_1(\varphi) = ie[H^+_{T1}(\varphi) - H^-_{T1}(\varphi)], \tag{5}$$

and the one from the right lead electrode to the island reads

$$I_2(\varphi) = ie[-H^+_{T2}(-\varphi) + H^-_{T2}(-\varphi)]. \tag{6}$$

By employing Kubo's formula for the SET-transistor, we find that for $\tau > 0$ its dc-conductance takes the following form

$$G_{dc} = \lim_{\omega\to 0} \omega^{-1} \Im m\{ \lim_{i\omega_l \to \omega + i\delta} e \int_0^\beta d\tau e^{i\omega_l \tau} \langle I(\tau) F(0)\rangle\}, \tag{7}$$

where $\{\omega_l\}$ are Matsubara frequencies with the definition $\omega_l = 2\pi l/\beta$, for $l = \pm 1, \pm 2, \cdots$ and $I(\tau)$ may be chosen as $I_1(\tau)$ or $-I_2(\tau)$, because $-I_2$ flows in the direction that the transport voltage decreases. It will be shown that they lead to the same result.

The undisturbed system is actually a single electron box (SEB) with two in-parallel connected tunnel junctions[4,10]. The partition function of this system may be described as a functional integral in the following form[2,13,14]

$$Z = \int D\varphi e^{-S_\Sigma[\varphi]}, \tag{8}$$

with the action

$$S_\Sigma[\varphi] = i n_{\rm ex}[\varphi(\beta) - \varphi(0)] + \int_0^\beta d\tau \frac{\dot\varphi^2(\tau)}{4E_c}$$
$$- \int_0^\beta d\tau \int_0^\beta d\tau' \alpha_\Sigma(\tau - \tau') \cos[\varphi(\tau) - \varphi(\tau')], \tag{9}$$

where $\alpha_\Sigma(\tau) = \alpha_1(\tau) + \alpha_2(\tau)$. Here $\alpha_i(\tau)$ is the damping kernel of the i-th tunnel junction, which is an even function with a period β and its Fourier transform reads[2,13,14]

$$\alpha_i(\tau) = \frac{1}{\beta} \sum_{l=-\infty}^{\infty} \alpha_i(\omega_l) e^{i\omega_l \tau}, \tag{10}$$

where

$$\alpha_i(\omega_l) = -\frac{\alpha_{ti}}{4\pi} |\omega_l|, \quad \text{for} \quad |\omega_l| \ll D. \tag{11}$$

Here $\alpha_{ti} = 4\pi^2 t_i^2 \rho_i \rho_i' N_i$, which is related to the tunnel resistance through $\alpha_{ti} = R_K/R_i$, and thus $\alpha_\Sigma(\tau) = \alpha_{t\Sigma}\alpha_i(\tau)/\alpha_{ti}$ with $\alpha_{t\Sigma} = \alpha_{t1} + \alpha_{t2}$. The bandwidth in metals D is normally much larger than the single electron charging energy E_c.

The current-current correlation functions may also be described in a path integral form by the generating functional approach as predicted by Ben-Jacob et al[13,15]. For the SET-transistor, we obtain for $i = 1$ or 2

$$\langle I_i(\tau) I_i(0)\rangle = Z^{-1} \int D\varphi e^{-S_\Sigma[\varphi]} \{2e^2 \alpha_i(\tau)$$
$$\times \cos[\varphi(\tau) - \varphi(0)] + I_{Ti}[\varphi, \tau] I_{Ti}[\varphi, 0]\} \tag{12}$$

and for $i \neq j$

$$\langle I_i(\tau) I_j(0)\rangle = Z^{-1} \int D\varphi e^{-S_\Sigma[\varphi]} I_{Ti}[\varphi, \tau] I_{Tj}[\varphi, 0], \tag{13}$$

where

$$I_{Ti}[\varphi, \tau] = -2e \int_0^\beta ds \alpha_i(\tau - s) \sin[\varphi(\tau) - \varphi(s)]. \tag{14}$$

From (9), we see that the action is a periodic function of φ with period 2π, and thus the partition function may be written as a sum over winding numbers, i.e.

$$Z = \sum_{k=-\infty}^{\infty} \int_{\varphi(\beta) = \varphi(0) + 2\pi k} D[\varphi] e^{-S_\Sigma[\varphi]}, \tag{15}$$

and so is the current auto-correlation function,

$$\langle I_i(\tau) I_i(0)\rangle = Z^{-1} \sum_{k=-\infty}^{\infty} \int_{\varphi(\beta) = \varphi(0) + 2\pi k} D[\varphi] e^{-S_\Sigma[\varphi]}$$
$$\{2e^2 \alpha_i(\tau) \cos[\varphi(\tau) - \varphi(0)] + I_{Ti}[\varphi, \tau] I_{Ti}[\varphi, 0]\}. \tag{16}$$

Due to the nonlinear, nonlocal interactions described by the damping part of the action, the partition function and correlation functions cannot be evaluated exactly. For a single tunnel junction or the SEB, there are some methods such as renormalization group theory, sluggish phase transition technique, quasiclassical Langevin equation, self-consistent harmonic approximation and Monte Carlo simulation developed to evaluate such functional integrals approximately or numerically[2,10,14–19]. At not too low temperatures the functional integrals may well be evaluated systematically as a series of βE_c by the semiclassical method including fluctuations beyond the Gaussian approximation as shown below.

From $\delta S_\Sigma[\varphi] = 0$ and the boundary condition $\varphi(\beta) = \varphi(0) + 2\pi k$ we get the trivial classical paths satisfying $\varphi_{\rm cl}^{(k)}(\tau) = \varphi(0) + \omega_k \tau$ with the classical action $S_{\rm cl}^{(k)} = \pi^2 k^2/\beta E_c + |k| \alpha_{t\Sigma}/2$. For an arbitrary path $\varphi(\tau) = \varphi_{\rm cl}^{(k)}(\tau) + \theta(\tau)$ of winding number k fluctuating about the classical solution, the second order variational action reads

$$\delta^2 S^{(k)} = \int_0^\beta d\tau \frac{\dot\theta^2}{4E_c} + \frac{1}{2} \int_0^\beta d\tau \int_0^\beta d\tau' \alpha_\Sigma(\tau - \tau')$$
$$\times \cos[\omega_k(\tau - \tau')][\theta(\tau) - \theta(\tau')]^2. \tag{17}$$

In terms of the Fourier transform $\theta(\tau) = \sum_{l=-\infty}^{\infty} \theta_l e^{i\omega_l \tau}$, with $\theta_l = \theta_l' + i\theta_l''$ and $\theta_{-l} = \theta_l^*$, one has

$$\delta^2 S^{(k)} = \sum_{l=1}^{\infty} \lambda_l^{(k)} ({\theta_l'}^2 + {\theta_l''}^2), \tag{18}$$

where for $l \ll \beta D$, the eigenvalues read

$$\lambda_l^{(k)} = \frac{\omega_l^2}{2E_c} + \Theta(l - |k|) \frac{\alpha_{t\Sigma}\, \omega_{l-|k|}}{2\pi}. \tag{19}$$

At high temperatures the eigenvalues are large and the trivial classical paths are stable. For very large l the eigenvalues approach $\omega_l^2/2E_c$ independent of k. Upon normalization of the path integral to the one of $k = 0$, the large l contributions cancel. It is then straightforward to show that

$$Z_{\rm semi} = Z_0 \left[1 + 2 \sum_{k=1}^{\infty} C_k \cos(2\pi k n_{\rm ex})\right], \tag{20}$$

where $Z_0 = \prod_{l=1}^{\infty} \pi/\beta\lambda_l^{(0)}$ is the contribution of paths with winding number 0 and

$$C_k = \frac{\Gamma(1+k_+)\Gamma(1+k_-)}{\Gamma^2(1+k)\Gamma(1+\mu_\Sigma)} e^{-S_{cl}^{(k)}},$$

where $\mu_\Sigma = \alpha_{t\Sigma}\beta E_c/2\pi^2$ and $k_\pm = k + \mu_\Sigma/2 \pm \sqrt{4\mu_\Sigma k + \mu_\Sigma^2}/2$.

The current-current correlation functions may be evaluated in the same way. In order to show the evaluation explicitly, we calculate here only $k = 0$ terms in detail, which are the dominating terms if the temperatures are not too low. Since for $\beta E_c \leq 1$, the semiclassical approach is well-behaved, the $k \neq 0$ terms are depressed at least by a factor of $\exp(-\pi^2/\beta E_c)$, and thus much smaller than the $k = 0$ terms. In this case the current auto-correlation function is approximately of the following form

$$\langle I_i(\tau) I_i(\tau')\rangle_f^{(0)} = 2e^2 \alpha_i(\tau - \tau') Z_{\text{semi}}^{-1} \int D\theta e^{-\delta^2 S[\theta]} \{1 - \frac{1}{2}[\theta(\tau) - \theta(\tau')]^2\}. \quad (21)$$

In the Fourier space, we have

$$\int D\theta e^{-\delta^2 S[\theta]} \{1 - \frac{1}{2}[\theta(\tau) - \theta(\tau')]^2\} = Z_0 \left\{ 1 - 2\sum_{l=1}^{\infty} \frac{1}{\beta\lambda_l^{(0)}} + 2\sum_{l=1}^{\infty} \frac{\cos\omega_l(\tau - \tau')}{\beta\lambda_l^{(0)}} \right\}. \quad (22)$$

Hence the corresponding conductance may be evaluated to give

$$\begin{aligned} G_{i,f}^{(0)} &= \lim_{\omega\to 0} \omega^{-1} \Im m\{ \lim_{i\omega_l \to \omega + i\delta} \int_0^\beta d\tau e^{i\omega_l \tau} \langle I_i(\tau) I_i(0)\rangle_f^{(0)} \} \\ &= \lim_{\omega\to 0} \omega^{-1} \Im m \left\{ \lim_{i\omega_l \to \omega + i\delta} (2e^2) \left[\alpha_i(\omega_l) - 2\sum_{n=1}^{\infty} \frac{\alpha_i(\omega_l)}{\beta\lambda_n^{(0)}} \right.\right. \\ &\left.\left. + \sum_{m=1}^{\infty} \frac{\alpha_i(\omega_m + \omega_l) + \alpha_i(\omega_m - \omega_l)}{\beta\lambda_m^{(0)}} \right] \right\}. \end{aligned} \quad (23)$$

The summations in the above equation may be carried out and finally we obtain

$$G_{i,f}^{(0)} = D_{01}/R_i \quad (24)$$

where the prefactor including the leading correction from fluctuations reads

$$D_{01} = 1 - 2[\Psi(\mu_\Sigma + 1) - \Psi(1)]/\alpha_{t\Sigma} - \beta E_c \Psi'(\mu_\Sigma + 1)/\pi^2. \quad (25)$$

Here the definition of the quantum resistance R_K has been used to get the final result. Note that we have taken $\hbar = 1$ in this paper for convenience.

The second term of the current auto-correlation function and the correlation function between currents through different tunnel junctions may be evaluated in the same manner. After some algebra we find that the terms from the correlation function between the currents of the same junction satisfy

$$\begin{aligned} G_{ii}^{(0)} &= \lim_{\omega\to 0} \omega^{-1} \Im m\{ \lim_{i\omega_l \to \omega + i\delta} \langle I_i(\tau) I_i(0)\rangle^{(0)} \} \\ &= \frac{D_{01}}{R_i} \left[1 - \frac{R_1 R_2}{R_i(R_1 + R_2)} \right], \end{aligned} \quad (26)$$

and the one between different tunnel junctions is of the following form

$$\begin{aligned} G_{ij}^{(0)} &= \lim_{\omega\to 0} \omega^{-1} \Im m\{ \lim_{i\omega_l \to \omega + i\delta} \langle I_i(\tau) I_j(0)\rangle^{(0)} \} \\ &= -\frac{D_{01}}{R_1 + R_2}. \end{aligned} \quad (27)$$

The total dc-conductance of the SET-transistor may be evaluated accordingly. The quantum conductance observed from the left tunnel junction reads

$$\begin{aligned} G_{dc}^{(L)} &= \lim_{\omega\to 0} \omega^{-1} \Im m\{ \lim_{i\omega_l \to \omega + i\delta} e \int_0^\beta d\tau e^{i\omega_l \tau} \langle I_1(\tau) F(0)\rangle^{(0)} \} \\ &= \kappa_1 G_{11}^{(0)} - \kappa_2 G_{12}^{(0)} \\ &= \frac{D_{01}}{R_1 + R_2}. \end{aligned} \quad (28)$$

Likewise, the conductance observed from the right junction takes the following form

$$\begin{aligned} G_{dc}^{(R)} &= -\lim_{\omega\to 0} \omega^{-1} \Im m\{ \lim_{i\omega_l \to \omega + i\delta} e \int_0^\beta d\tau e^{i\omega_l \tau} \langle I_2(\tau) F(0)\rangle^{(0)} \} \\ &= -\kappa_1 G_{21}^{(0)} + \kappa_2 G_{22}^{(0)} \\ &= \frac{D_{01}}{R_1 + R_2}, \end{aligned} \quad (29)$$

which is exactly the same as $G_{dc}^{(L)}$.

For $\mu_\Sigma \ll 1$, the factor D_{01} may be simplified to give

$$D_{01}^{(n)} = 1 - \beta E_c/3 + \mathcal{O}[(\beta E_c)^2]. \quad (30)$$

In the high temperature limit, the ohmic behavior $G_{ohm} = 1/(R_1 + R_2)$ is recovered. Up to the order of βE_c, this result is in good agreement with the one by exploiting Fermi golden rule[8,9,11]. Note that (28) or (29) are also valid for the SET-transistor formed by tunnel junctions with different resistances and capacitances, while by directly taking the tunnel Hamiltonian as a perturbation to calculate the quantum conductance analytically the junctions are taken to be identical[8,9].

An anomaly of the quantum conductance occurs if one or both of the tunnel resistances are much smaller than R_K so that $\alpha_{t\Sigma} \gg \pi^2/\beta E_c \gg 1$. Since the form of D_{01} holds only if βE_c is very small, we have then

$$D_{01}^{(a)} = 1 - 2[\ln(\alpha_{t\Sigma}) + \ln(\beta E_c)]/\alpha_{t\Sigma} + \mathcal{O}(1/\alpha_{t\Sigma}). \quad (31)$$

This anomalous relation may be observed only under the above-mentioned strict conditions, the calculation here, however, shows that the linear dependence of the leading correction of the quantum conductance on βE_c is generally not valid if $\alpha_{t\Sigma} > \pi^2/\beta E_c$.

The quantum conductance of the SET-transistor as a series of βE_c may be evaluated further if higher orders of the expansion of the action, $\cos[\theta(\tau) - \theta(\tau')]$ and $\sin[\theta(\tau) - \theta(\tau')]$ in (12) are taken into account. To the order of $(\beta E_c)^2$ we obtain that the quantum conductance of the SET-transistor for $\alpha_{t\Sigma} < 1/\beta E_c$ takes the same form as (28) or (29), yet with a prefactor

$$D_{02} = D_{01} + [0.0667 + 0.0185\alpha_{t\Sigma}](\beta E_c)^2 + \mathcal{O}[(\beta E_c)^3] \tag{32}$$

instead of D_{01}. Higher orders of βE_c may also be determined in the same way. It will be very tedious to calculate such terms and a finite number of terms in the series is probably not enough to predict the behavior of the SET-transistor at low temperatures, because the series is an asymptotic one. At low temperatures more sophisticated techniques are needed to evaluate the path integrals instead of the simple semiclassical method[2,10,14–19].

The quantum conductance of the SET-transistor is an oscillating function of the gate voltage if the terms with $k \neq 0$ are taken into account. Then the quantum conductance of the SET-transistor as a function of the gate voltage is found to be

$$G_{dc} = \frac{D_0 + 2C_1 D_1 \cos(2\pi n_{\rm ex})}{R_1 + R_2}, \tag{33}$$

where at high temperatures the explicit form of D_0 is given by (25) or (32) and the leading term of D_1 reads

$$D_{1,l} = -4\pi^2/\beta E_c - \alpha_{t\Sigma} + 2 + 2\pi^2/3 + \mathcal{O}(\beta E_c). \tag{34}$$

In summary, quantum conductance of the SET-transistor as a function of the gate voltage has been discussed in this work. By employing the functional integral approach we have obtained the general formula of the quantum conductance, which is valid for arbitrary tunnel resistance of the junctions forming the SET-transistor at any temperature. At not too low temperatures the path integrals have been evaluated by the semiclassical method to yield an explicit form of the quantum conductance. This result gives clear criterions to the application of the SET-transistor as e.g. a new kind of thermometers insensitive to magnetic field by taking advantage of the linear dependence of the quantum conductance on βE_c[8]. We have also proved that under typically experimental conditions the linear dependence of the quantum conductance on βE_c is also valid for the SET-transistor formed by tunnel junctions with different parameters. If the tunnel resistances are much smaller the quantum resistance, an anomaly of the quantum conductance has also been studied. Our treatment is nonperturbative and includes also the dependence of the quantum conductance on the gate voltage. At low temperatures the trivial classical paths are no more stable, thus the derived path integrals must be evaluated by methods other than the simple semiclassical approach so that large quantum fluctuations are properly treated.

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